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PCN #149

**Notification Date:
30 May 2014**

Product / Process Change Notice

Parts Affected:

Chip process CP117, NPN silicon, Darlington power transistors, wafers, and bare die.

Extent of Change:

The CP117 wafer process has been discontinued and replaced with the CP127 wafer process.

The overall wafer diameter is being reduced from 5 inch to 4 inch.

The die pattern has been changed; see figures 1 and 2 for details.

Reason for Change:

This process was transferred to an alternate wafer foundry due to low volume production.

Effect of Change:

The wafer process meets all electrical specifications of the individual devices listed on the following page.

Qualification:

Standard evaluation and qualifications completed resulting in no performance degradation.

Effective Date of Change:

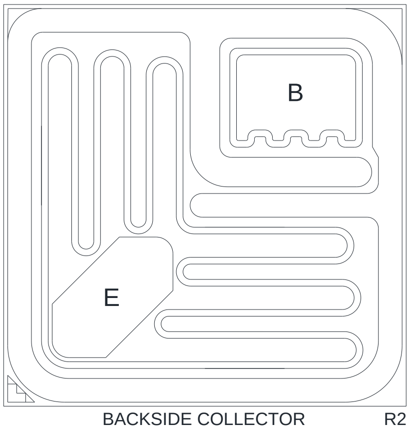
Existing inventory will be shipped until depleted.

Sample Availability:

Please contact Salesperson or Manufacturer’s Representative.

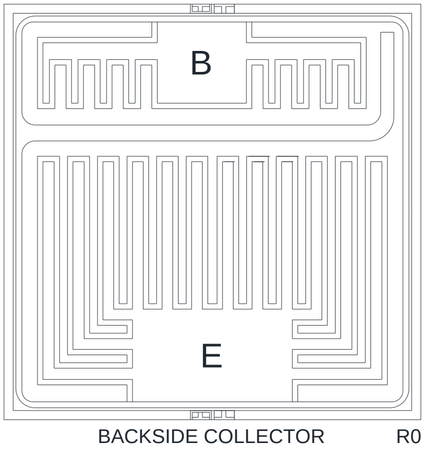
Figures:

Figure 1: CP117 Chip Geometry (Discontinued)



Wafer Diameter:	5 inch
Die Size:	111 x 111 mils
Die Thickness:	11 mils
Bond Pad Size (Emitter):	20 x 26 mils
Bond Pad Size (Base):	20 x 30 mils
Topside Metal:	Al (60,000Å)
Backside Metal:	Au/Cr/Ni/Au (6,100Å)

Figure 2:CP127 Chip Geometry



Wafer Diameter:	4 inch
Die Size:	110 x 110 mils
Die Thickness:	10.6 mils
Bond Pad Size (Emitter):	24 x 42 mils
Bond Pad Size (Base):	21 x 24 mils
Topside Metal:	Al (20,000Å)
Backside Metal:	Ag (10,000Å)

Part Numbers Affected:

2N6300
2N6301
2N6294
2N6295
CP117-TIP112-CT
CP117-TIP121-CT
CP117-TIP122-CT
CP117-2N6045-CT
CP117-2N6294-CT
CP117-2N6300-CT
CP117-2N6301-CT
CP117-2N6385-CT
CEN781
CEN1228